

IN THE CLAIMS:

1. (Previously Presented) A semiconductor device comprising:
a gate electrode formed over a substrate;
a gate insulating film formed over the gate electrode;
a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and
source and drain regions comprising silicon formed on said semiconductor film,
wherein a peak position of a Raman spectrograph of said semiconductor film is lower than 520 cm^{-1} .
2. (Original) The semiconductor device according to claim 1 wherein said gate electrode comprises molybdenum.
3. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide.
4. (Previously Presented) A semiconductor device comprising:
a gate electrode formed over a substrate;
a gate insulating film formed over the gate electrode;
a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and
source and drain regions comprising silicon formed on said semiconductor film,
wherein a peak position of a Raman spectrograph of said semiconductor film is lower than 520 cm^{-1} and said semiconductor film has a distortion in the lattice.
5. (Original) The semiconductor device according to claim 4 wherein said gate electrode comprises molybdenum.

6. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide.
7. (Currently Amended) A semiconductor device comprising:
 - a gate electrode formed over a substrate;
 - a gate insulating film formed over the gate electrode;
 - a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed therebetween, said semiconductor film including a channel formation region and
 - source and drain regions comprising silicon formed on said semiconductor film, wherein a peak position of a Raman spectrograph of said semiconductor film is lower than 520 cm^{-1} and said semiconductor film has a distortion in the lattice, and the semiconductor film has no barrier against ~~earners~~ carriers at grain boundaries.
8. (Original) The semiconductor device according to claim 7 wherein said gate electrode comprises molybdenum.
9. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide.
10. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide containing fluorine.
11. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide containing fluorine.
12. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide containing fluorine.